

**Dedicated to the memory of Prof. M. Sheinkman effect of ultrasonic treatment on the defect structure of the Si-SiO<sub>2</sub> system**

**Kropman, Daniel;** Dolgov, Sergei; Onufrijevs, Pavels; Dauksta, Edvins Gettering and Defect Engineering in Semiconductor Technology XV 2014 / p. 352-357 : ill <https://doi.org/10.4028/www.scientific.net/SSP.205-206.352> [Conference proceedings at Scopus](#) [Article at Scopus](#) [Conference proceedings at WOS](#) [Article at WOS](#)

**Low-K factor of SiO<sub>2</sub> layer on Si irradiated by YAG:Nd laser**

Medvid, A.; Onufrijevs, Pavels; **Melikov, Enn;** **Kropman, Daniel;** Muktepavela, F.; Bakradze, G. Journal of non-crystalline solids 2007 / p. 703-707 : ill <https://www.sciencedirect.com/science/article/pii/S0022309306014116>

**Stress relaxation mechanism by strain in the Si-SiO<sub>2</sub> system and its influence on the interface properties**

**Kropman, Daniel;** **Melikov, Enn;** Kärner, Tiit; Laas, Tõnu; Medvid, Arthur; Onufrijevs, Pavels; Dauksta, Edvins Solid state phenomena 2011 / p. 259-262

**Understanding and control of stress at Si-SiO<sub>2</sub> interface**

Kropman, Daniel; Seeman, Viktor; Medvids, Arturs; Onufrijevs, Pavels; Vitusevich, Svetlana; **Mikli, Valdek** Key engineering materials 2020 / p. 291-296 <https://doi.org/10.4028/www.scientific.net/KEM.850.291> [Journal metrics at Scopus](#) [Article at Scopus](#)